

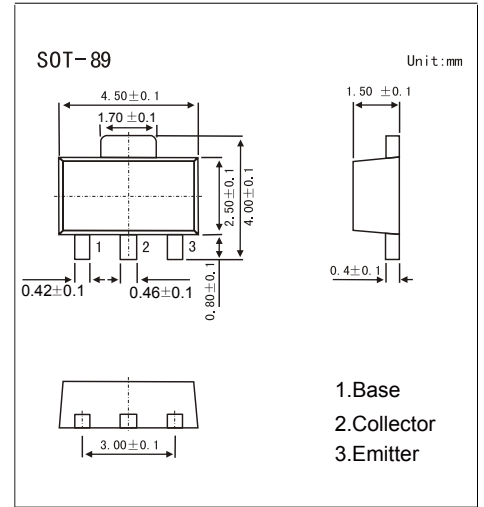
SOT-89 Plastic-Encapsulate Transistors

Features

- Low Saturation Voltage
- Excellent hFE Characteristics
- Complementary to 2SA1797
- NPN Transistors

MECHANICAL DATA

- Case style:SOT-89 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	60	V
Collector - Emitter Voltage	V _{CEO}	50	
Emitter - Base Voltage	V _{EBO}	6	
Collector Current - Continuous	I _c	2	A
Collector Power Dissipation	P _c	500	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	250	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = 50 μA, I _E = 0	60			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = 1 mA, I _B = 0	50			
Emitter - base breakdown voltage	V _{EBO}	I _E = 50 μA, I _c = 0	6			
Collector-base cut-off current	I _{CB0}	V _{CB} = 60V, I _E = 0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _c =0			0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =1A, I _B =50mA			0.35	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c =1A, I _B =50mA			1.2	
DC current gain	h _{FE}	V _{CE} = 2V, I _c = 500mA	82		390	
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f=1MHz		25		pF
Transition frequency	f _t	V _{CE} = 2V, I _c = 500mA, f=100MHz		210		MHz

Classification of h_{FE}

Type	2SC4672-P	2SC4672-Q	2SC4672-R
Range	82-180	120-270	180-390
Marking	DKP	DKQ	DKR

RATINGS AND CHARACTERISTIC CURVES

■ Typical Characteristics

